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# FQPF2N80YDTU

## N-Channel QFET® MOSFET

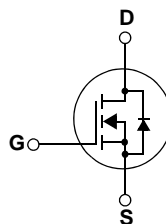
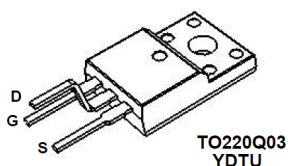
80 V, 1.5 A, 80 mΩ

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 1.5 A, 80 V,  $R_{DS(on)} = 80 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 0.75 \text{ A}$
- Low Gate Charge (Typ. 12 nC)
- Low  $C_{rss}$  (Typ. 5.5 pF)
- 100% Avalanche Tested



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQPF2N80YDTU	Unit
$V_{DSS}$	Drain-Source Voltage	800	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	1.5	A
		0.95	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	6.0	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	5.2	mJ
$I_{AR}$	Avalanche Current (Note 1)	1.5	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	3.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	35	W
		0.28	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FQPF2N80YDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.57	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	800	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.9	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.75\text{ A}$	--	4.9	6.3	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.75\text{ A}$	--	2.2	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	425	550	pF
$C_{oss}$	Output Capacitance		--	45	60	pF
$C_{riss}$	Reverse Transfer Capacitance		--	5.5	7.0	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 2.4\text{ A}, R_G = 25\ \Omega$	--	12	35	ns	
$t_r$	Turn-On Rise Time		--	30	70	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	25	60	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	28	65	ns
$Q_g$	Total Gate Charge	$V_{DS} = 640\text{ V}, I_D = 2.4\text{ A}, V_{GS} = 10\text{ V}$	--	12	15	nC	
$Q_{gs}$	Gate-Source Charge		(Note 4)	--	2.6	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	6.0	--	nC

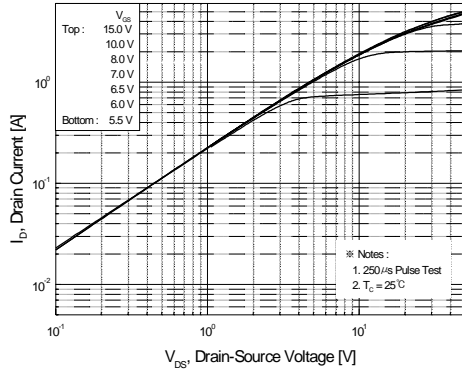
### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.5	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	6.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.5\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 2.4\text{ A}, di_F / dt = 100\text{ A}/\mu\text{s}$	--	480	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	2.0	--	$\mu\text{C}$

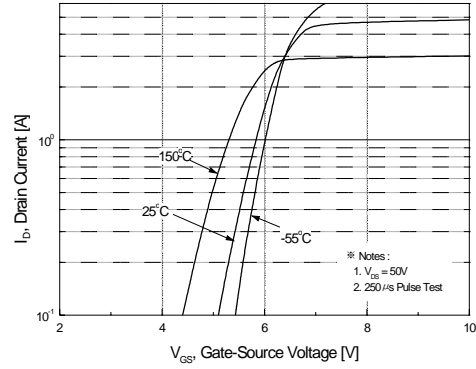
#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 4.3\text{ mH}, I_{AS} = 1.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 2.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

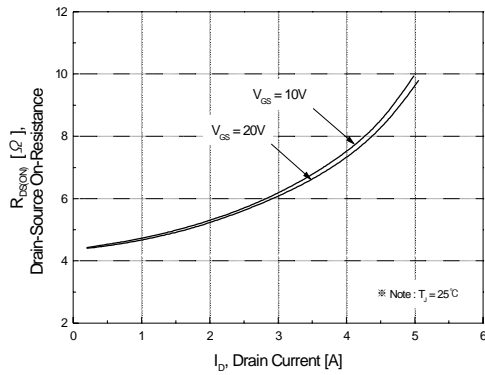
## Typical Characteristics



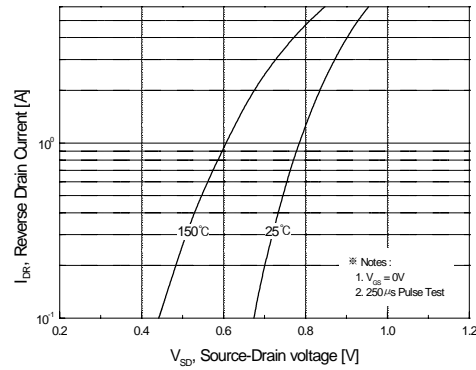
**Figure 1. On-Region Characteristics**



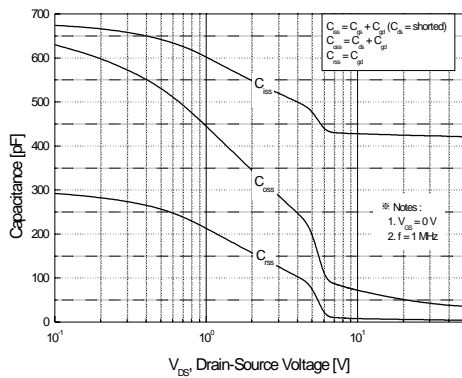
**Figure 2. Transfer Characteristics**



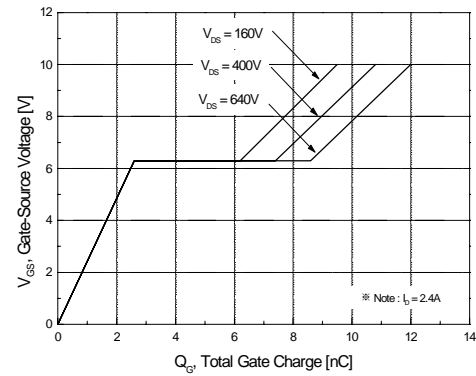
**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

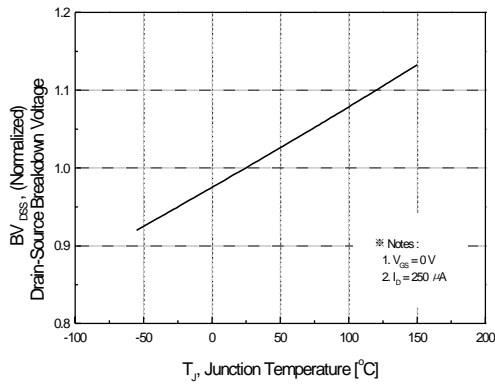


**Figure 5. Capacitance Characteristics**

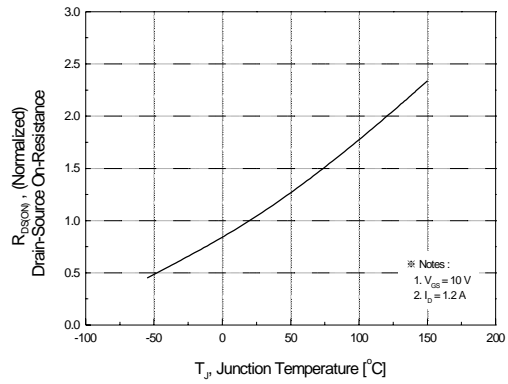


**Figure 6. Gate Charge Characteristics**

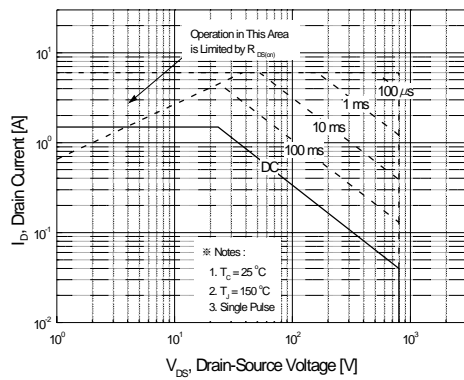
**Typical Characteristics** (Continued)



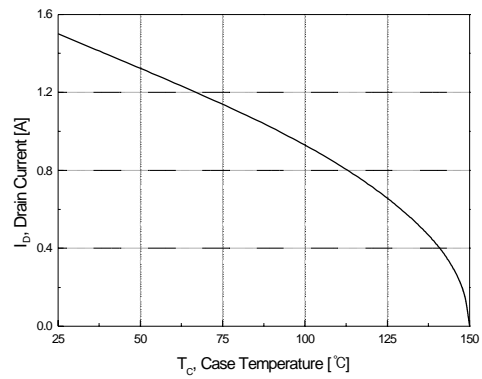
**Figure 7. Breakdown Voltage Variation vs Temperature**



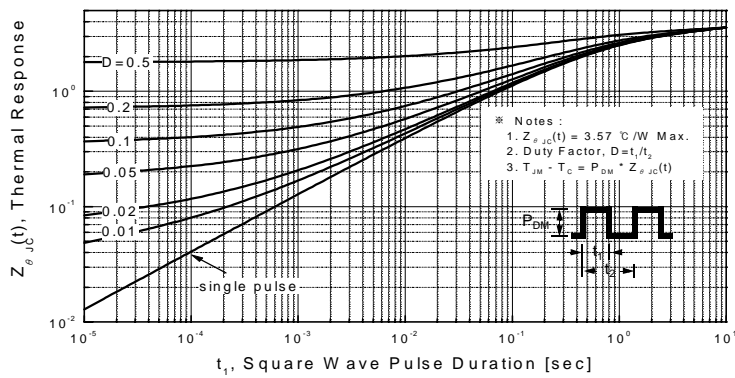
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9. Maximum Safe Operating Area**

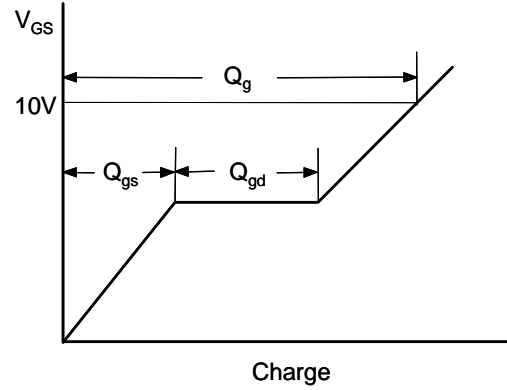
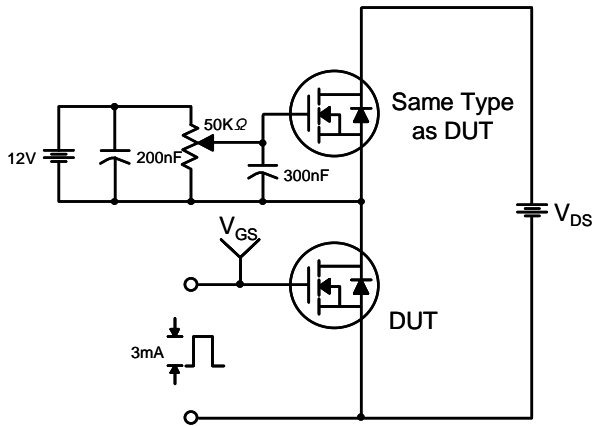


**Figure 10. Maximum Drain Current vs Case Temperature**

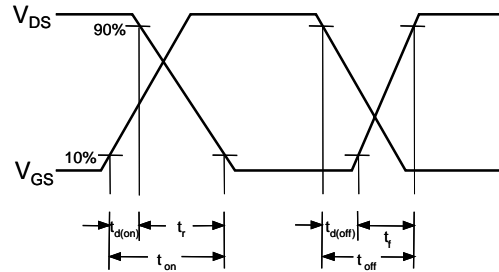
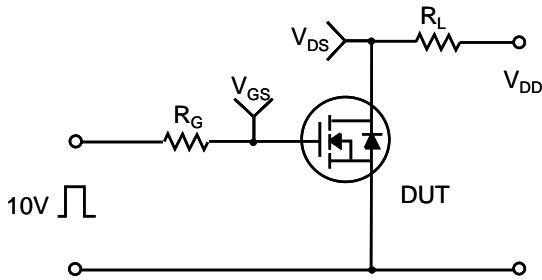


**Figure 11. Transient Thermal Response Curve**

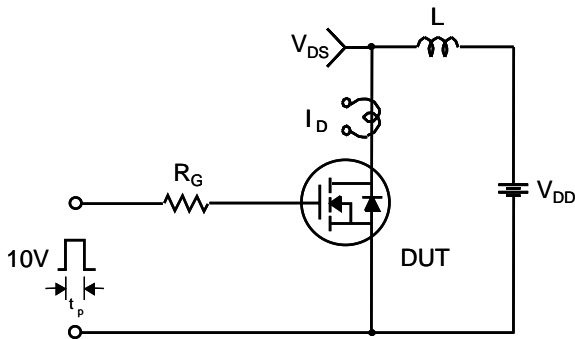
**Gate Charge Test Circuit & Waveform**



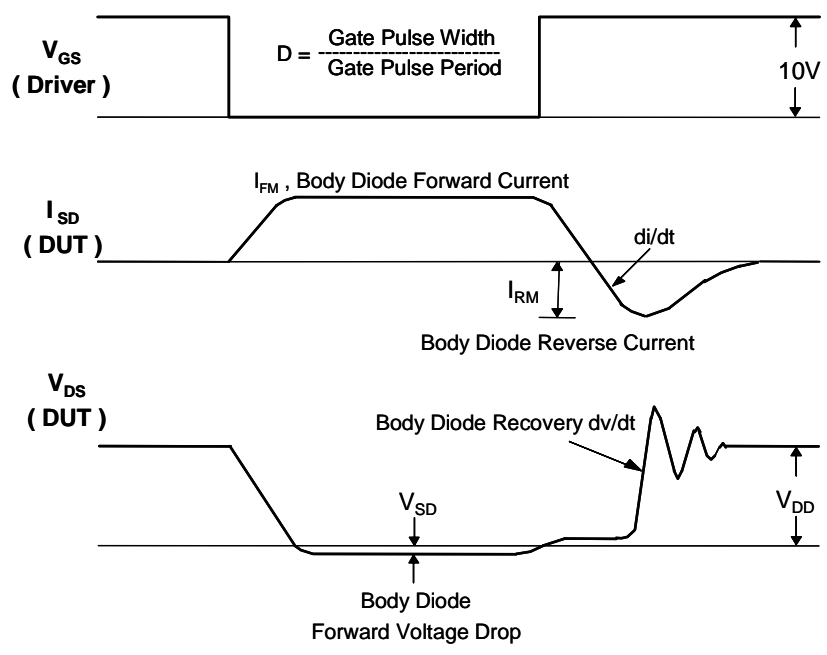
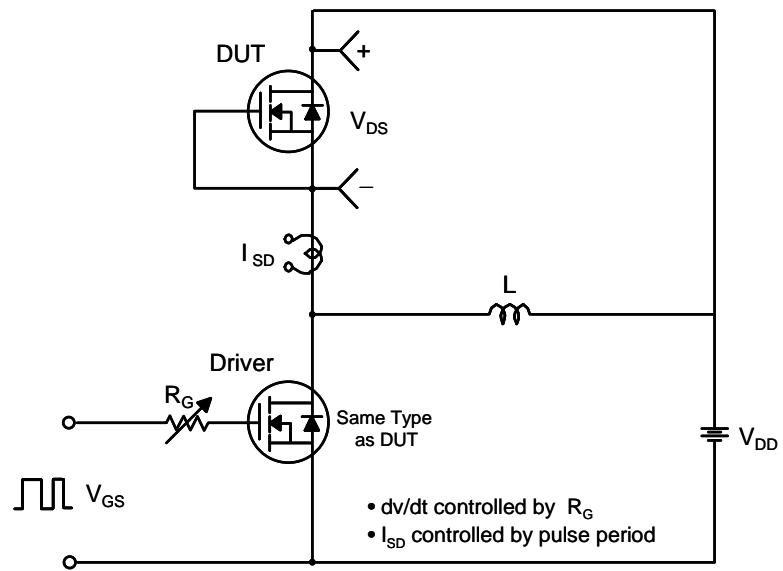
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

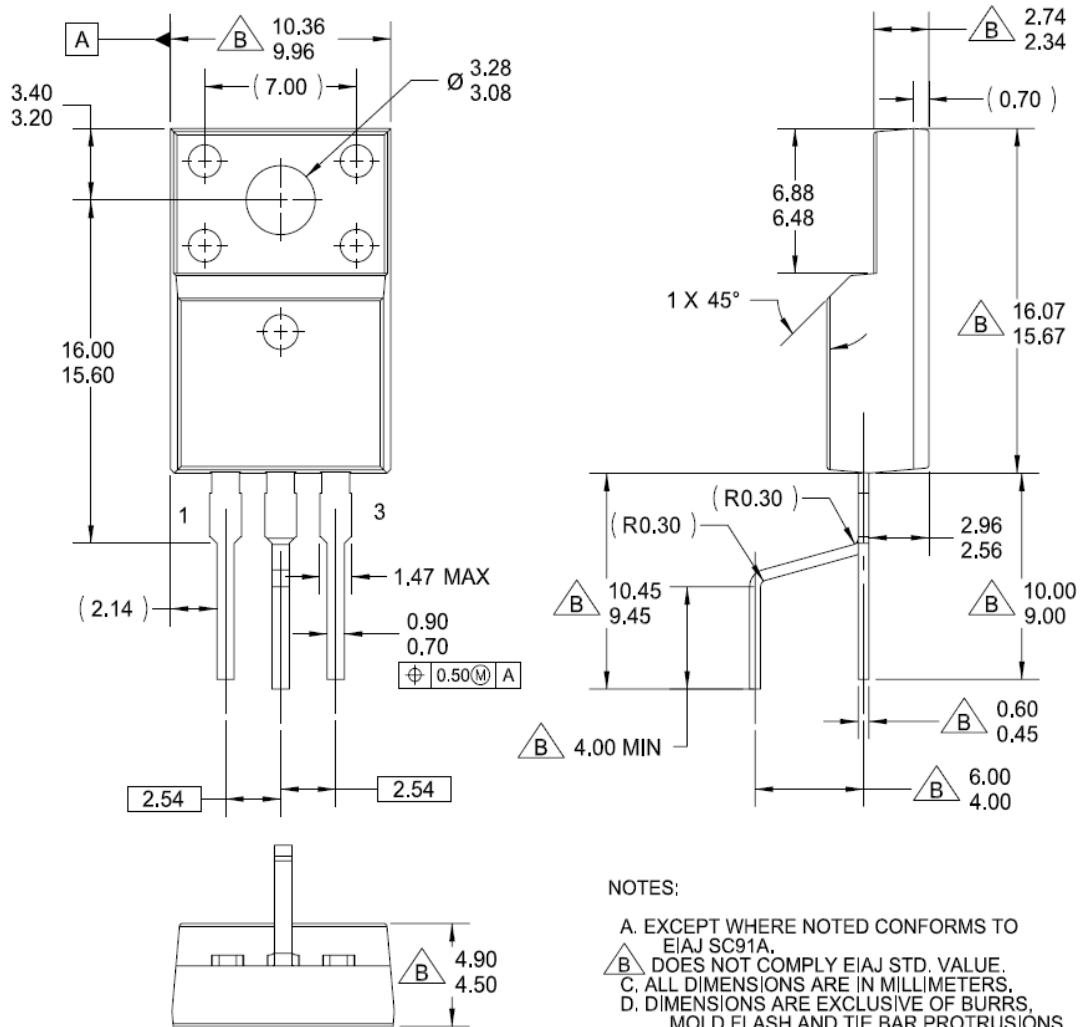


Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

# TO220Q03



### NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. DRAWING FILE NAME: TO220Q03REV1

### TO-220F 3L - TO220, MOLDED, 3LD, FULL PACK, EIAJ SC91, Y FORMED LEAD

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Dimensions in Millimeters





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